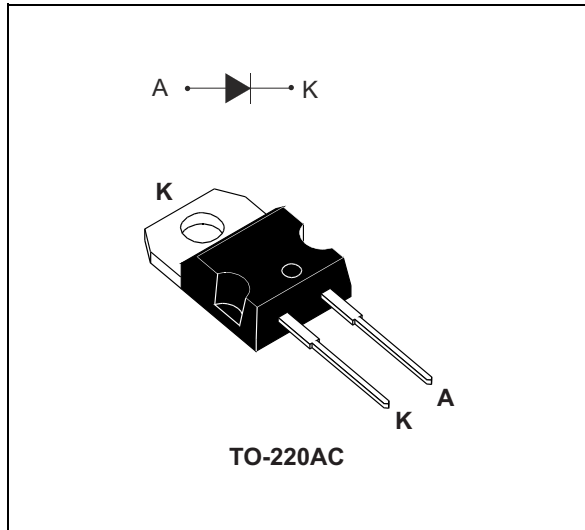


Automotive 650 V power Schottky silicon carbide diode

Datasheet - production data



Description

The SiC diode is an ultrahigh performance power Schottky diode. It is manufactured using a silicon carbide substrate. The wide band gap material allows the design of a Schottky diode structure with a 650 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature and are ideal for automotive applications.

Especially suited for use in PFC applications, this ST SiC diode will boost the performance in hard switching conditions. Its high forward surge capability ensures a good robustness during transient phases.

Features

- No reverse recovery charge in application current range
- Switching behavior independent of temperature
- Dedicated to PFC applications
- High forward surge capability
- AEC-Q101 qualified
- PPAP capable
- ECOPACK[®]2 compliant component

Table 1. Device summary

Symbol	Value
$I_{F(AV)}$	10 A
V_{RRM}	650 V
T_j (max)	175 °C

1 Characteristics

Table 2. Absolute ratings (limiting values at 25 °C unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		650	V
$I_{F(RMS)}$	Forward rms current		22	A
$I_{F(AV)}$	Average forward current	$T_C = 135\text{ °C}^{(1)}$, DC	10	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10\text{ ms}$ sinusoidal, $T_C = 25\text{ °C}$	90	A
		$t_p = 10\text{ ms}$ sinusoidal, $T_C = 125\text{ °C}$	80	
		$t_p = 10\text{ }\mu\text{s}$ square, $T_C = 25\text{ °C}$	470	
I_{FRM}	Repetitive peak forward current	$T_C = 135\text{ °C}^{(1)}$, $T_j = 175\text{ °C}$, $\delta = 0.1$	41	A
T_{stg}	Storage temperature range		-55 to +175	°C
T_j	Operating junction temperature ⁽²⁾		-40 to +175	°C

- Value based on $R_{th(j-c)}$ max.
- $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$ condition to avoid thermal runaway for a diode on its own heatsink

Table 3. Thermal resistance

Symbol	Parameter	Typ. value	Max. value	Unit
$R_{th(j-c)}$	Junction to case	1.25	1.5	°C/W

Table 4. Static electrical characteristics

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25\text{ °C}$	$V_R = V_{RRM}$	-	9	100	μA
		$T_j = 150\text{ °C}$		-	85	425	
$V_F^{(2)}$	Forward voltage drop	$T_j = 25\text{ °C}$	$I_F = 10\text{ A}$	-	1.56	1.75	V
		$T_j = 150\text{ °C}$		-	1.98	2.5	

- Pulse test: $t_p = 5\text{ ms}$, $\delta < 2\%$
- Pulse test: $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 1.35 \times I_{F(AV)} + 0.115 \times I_{F(RMS)}^2$$

Table 5. Dynamic electrical characteristics

Symbol	Parameter	Test conditions	Typ.	Unit
$Q_{cj}^{(1)}$	Total capacitive charge	$V_R = 400\text{ V}$,	28.5	nC
C_j	Total capacitance	$V_R = 0\text{ V}$, $T_C = 25\text{ °C}$, $F = 1\text{ MHz}$	480	pF
		$V_R = 400\text{ V}$, $T_C = 25\text{ °C}$, $F = 1\text{ MHz}$	48	

- Most accurate value for the capacitive charge: $Q_{cj} = \int_0^{V_{OUT}} C_j(V_R) \cdot dV_R$

Figure 1. Forward voltage drop versus forward current (typical values, low level)

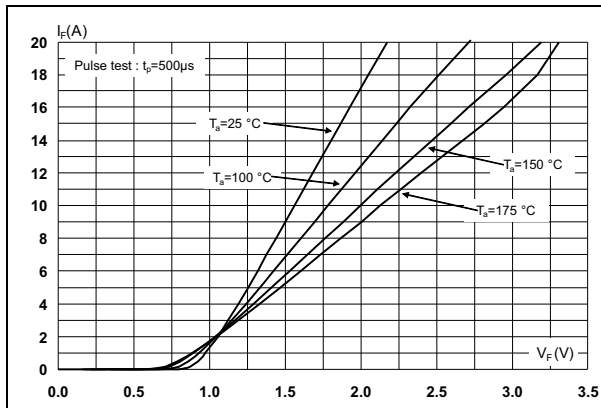


Figure 2. Forward voltage drop versus forward current (typical values, high level)

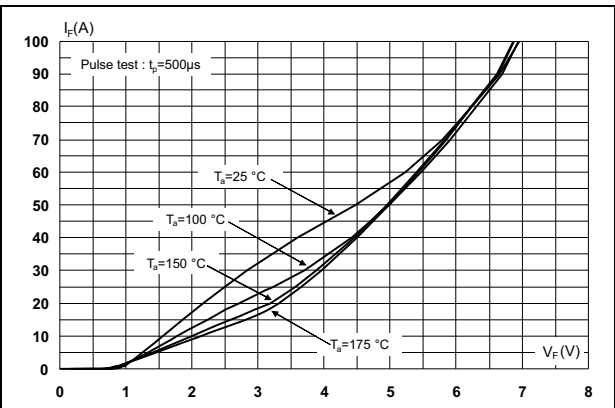


Figure 3. Reverse leakage current versus reverse voltage applied (typical values)

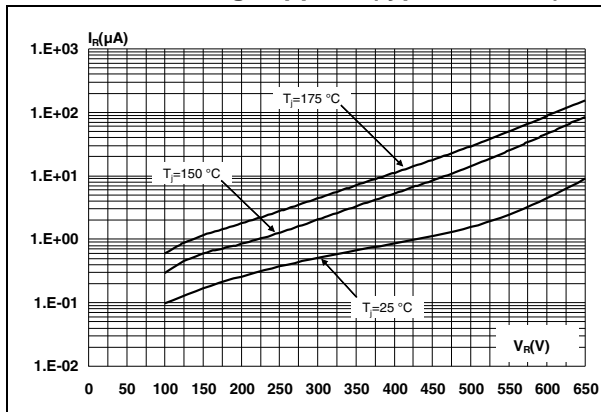


Figure 4. Peak forward current versus case temperature (TO-220AC)

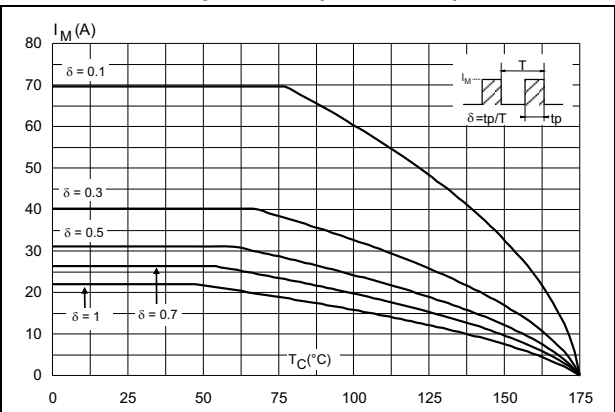


Figure 5. Junction capacitance versus reverse voltage applied (typical values)

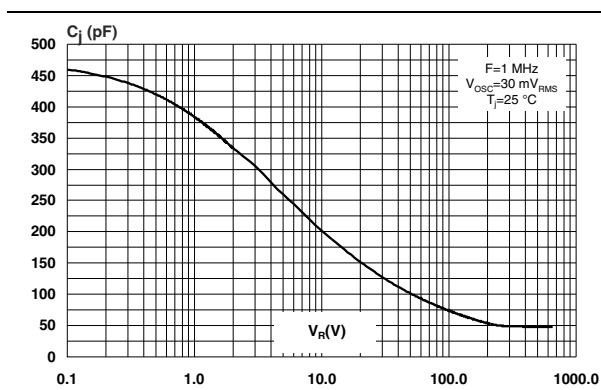


Figure 6. Relative variation of thermal impedance junction to case versus pulse duration (TO-220AC)

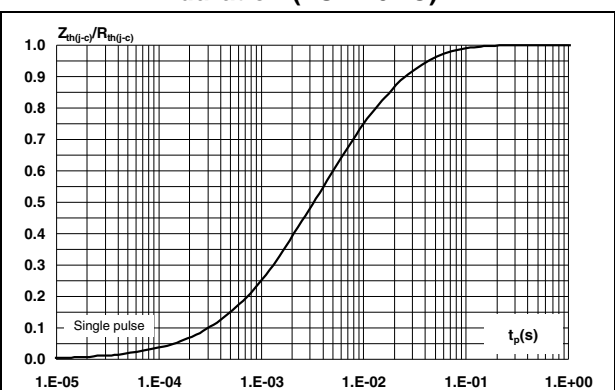


Figure 7. Non-repetitive peak surge forward current versus pulse duration (sinusoidal waveform)

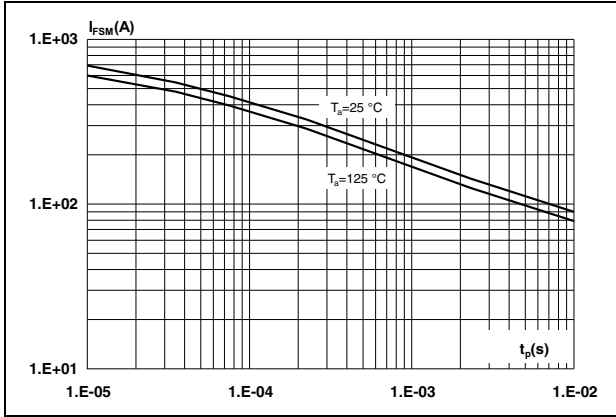


Figure 8. Total capacitive charges versus reverse voltage applied (typical values)

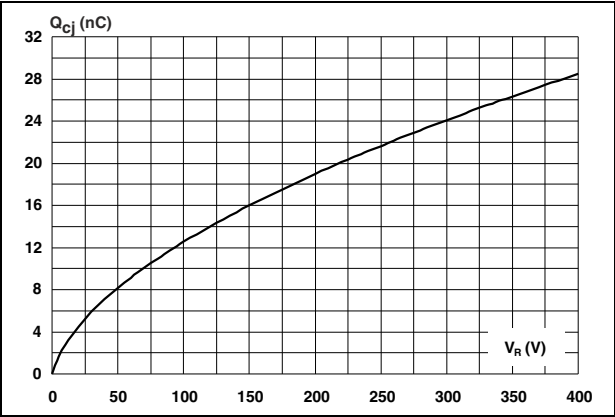


Table 6. TO-220AC dimension values

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
C	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
E	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
H2	10.00	10.40	0.393	0.409
L2	16.40 typ.		0.645 typ.	
L4	13.00	14.00	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
M	2.6 typ.		0.102 typ.	
Diam. I	3.75	3.85	0.147	0.151

3 Ordering information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPSC10H065DY	PSC10H065DY	TO-220AC	1.86 g	50	Tube

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
26-Jun-2014	1	First issue.
19-Sep-2014	2	Updated Table 7 .

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